

In the Claims:

1.-23. (Cancel)

24. (Currently Amended) A transistor comprising:

a semiconductor body;

a source disposed in the semiconductor body;

a drain disposed in the semiconductor body and spaced from the source by a channel;

a gate dielectric overlying the channel;

a polysilicon layer overlaying the gate dielectric;

a barrier layer overlying and in physical contact with the polysilicon layer ~~the gate dielectric~~, the barrier layer comprising a single layer of WN_x , wherein x is a constant value between 0.3 and 0.5; and

a gate conductor overlying and in physical contact with the barrier layer, said gate conductor ~~being comprising tungsten metal~~.

25.-27. (Cancel)

28. (Previously Presented) The transistor of claim 24 wherein the barrier layer has a thickness in the range of 1 to 50 nm.

29. (Currently Amended) A transistor gate stack formed of layers comprising:

a conductive polysilicon layer;

a solitary barrier layer overlying and in physical contact with said conductive polysilicon

layer, said barrier layer formed from WN_x , where x equals a specific selected value between 0.3 and 0.5; and

a ~~tungsten (W)~~ conductive layer made of tungsten (W) overlying and in physical contact with said barrier layer to form the gate electrode of said transistor.